

FEATURES

- Input voltage at pin DRAIN $20\text{ V} \leq V_{IN} \leq 400\text{ V}$
- Operating temperature range: $-40\text{ }^{\circ}\text{C}$ to $85\text{ }^{\circ}\text{C}$
- Resistance of the DRAIN-GND open key in on condition of R_{ON} is not more than $40\ \Omega$ at the ambient temperature of $25\text{ }^{\circ}\text{C}$
- Breakdown voltage of the closed key at the pin DRAIN V_{BR} not less than 460 V
- Average stabilization current at pin DRAIN: $120\text{ mA} \pm 5\%$
- Load Short circuit protection
- Overheating protection

APPLICATION

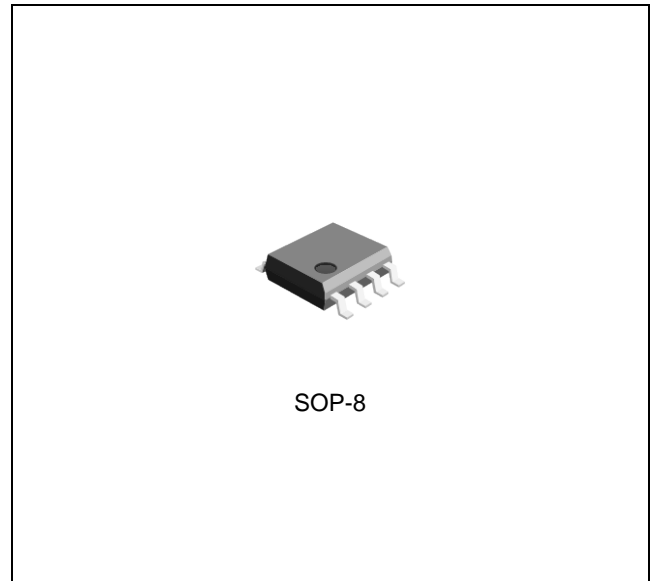
- DC/DC or AC/DC LED Driver
- Decorative Lighting

DESCRIPTION

The TJ33120 is high voltage LED driver with the internal MOSFET is intended for LED chain control.

The TJ33120 ensures control and stabilization of the current average value in the LED circuit by means of commutation the current pulses in the inductor in the PWM mode with the fixed switch-off time with application of the built-in MOSFET switch. IC contains the internal high voltage MOSFET switch with the voltage of 400 V , voltage regulator, reference voltage source, switch-off time countdown timer, control circuit of the current average value in the LED circuit, overheating and load short-circuit protection circuits, digital logic control circuits and analog comparators.

TJ33120 can be supplied from the DC input voltage of 20 V to 400 V or the AC input voltage 85 V to 265 V .



ORDERING INFORMATION

| Device | Package |
|-----------|---------|
| TJ33120GD | SOP-8 |

* For the details, see ordering information.

ABSOLUTE MAXIMUM RATINGS (Note 1)

| CHARACTERISTIC | SYMBOL | MIN. | MAX. | UNIT |
|-------------------------------------|-------------|------|------|--------------------|
| Input DRAIN Voltage (Survival) | V_{DRAIN} | -0.3 | 420 | V |
| Input VDD Voltage (Survival) | V_{DD} | -0.3 | 10 | V |
| Lead Temperature (Soldering, 5 sec) | T_{SOL} | | 260 | $^{\circ}\text{C}$ |
| Storage Temperature Range | T_{STG} | -65 | 150 | $^{\circ}\text{C}$ |

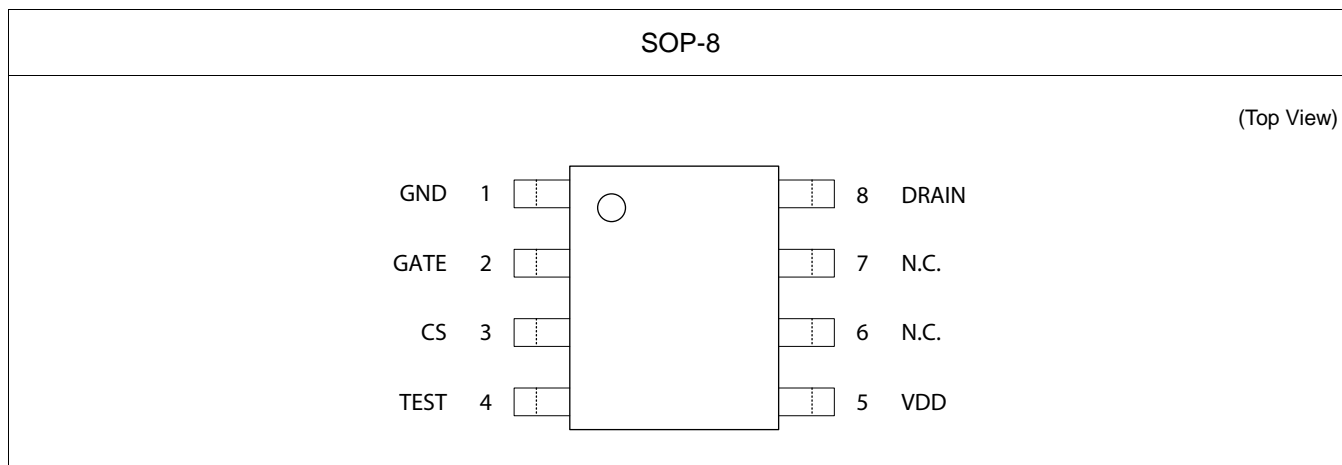
RECOMMENDED OPERATING RATINGS (Note 2)

| CHARACTERISTIC | SYMBOL | MIN. | MAX. | UNIT |
|---------------------------------------|-------------|------|------|------|
| Input DRAIN Voltage | V_{DRAIN} | 20 | 400 | V |
| Recommend Operating Input Voltage | V_{DD} | 5.0 | 9.5 | V |
| Operating Junction Temperature Range | T_{JOPR} | -40 | 125 | °C |
| Recommend Operating Temperature Range | T_A | -40 | 85 | °C |

ORDERING INFORMATION

| Order No. | Package | Description | Supplied As | Status |
|-----------|---------|------------------------|-------------|--------|
| TJ33120GD | SOP-8 | 120mA, Internal MOSFET | Reel | Active |

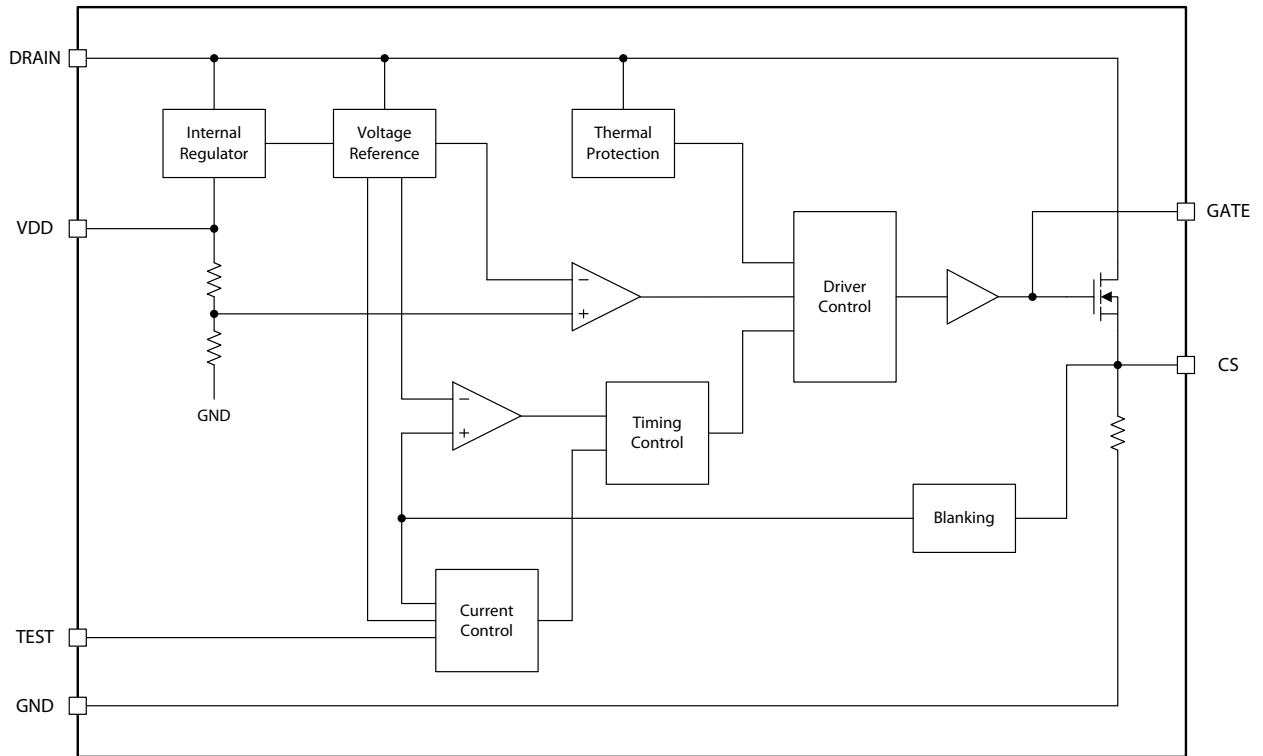
PIN CONFIGURATION



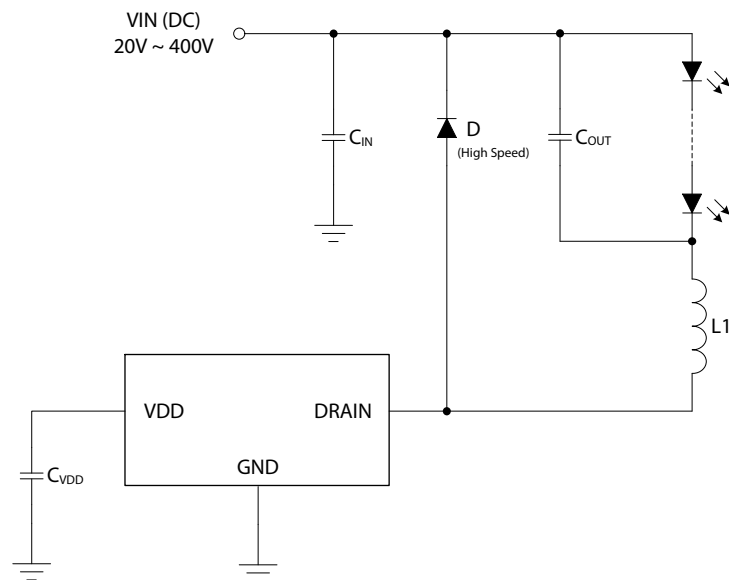
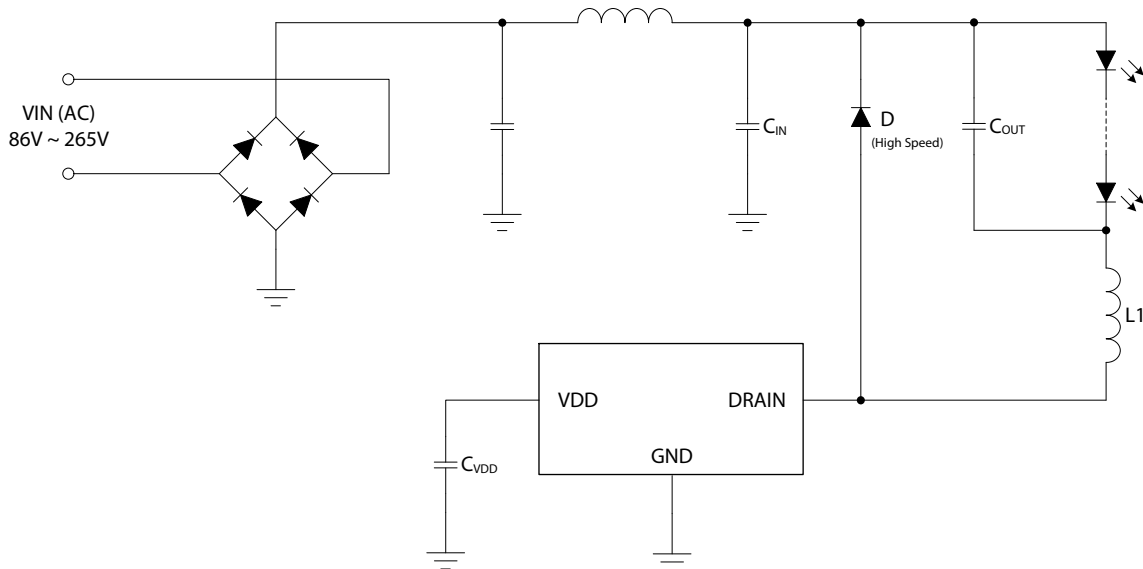
PIN DESCRIPTION

| Pin No. | Pin Name | Pin Description |
|---------|----------|---|
| 1 | GND | Ground |
| 2 | GATE | (Internal Use/ Float this pin) Gate |
| 3 | CS | (Internal Use/ Float this pin) Current Sense |
| 4 | TEST | (Internal Use/ Float this pin) Test for Internal Function |
| 5 | VDD | Supply from the Voltage Source |
| 6 | N.C. | Not Connected |
| 7 | N.C. | Not Connected |
| 8 | DRAIN | Drain Terminal of the Internal MOSFET |

BLOCK DIAGRAM



TYPICAL APPLICATION



ELECTRICAL CHARACTERISTICS (Note 3)

Limits in standard typeface are for $T_J=25^{\circ}\text{C}$, and limits in **boldface type** apply over the **full operating temperature range**.

| PARAMETER | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|-----------------------------------|----------------------|--|-------------------|------|--|---------------|
| Internal Regulator Output Voltage | V_{DDR} | $V_{\text{IN}} = 20\text{ V}, V_{\text{IN}} = 400\text{ V}$ | 5.5 5.0 | - | 8.5 9.5 | V |
| Input UVLO Threshold | V_{UVLO} | $V_{\text{DD}} = V_{\text{UVLO}}$ | 4.0 3.8 | - | $V_{\text{DDR}}-0.3\text{V}$ $V_{\text{DDR}}-0.1\text{V}$ | V |
| Supply Current | I_{DD} | $V_{\text{DD}} = V_{\text{DDR}} + 0.2\text{ V}, V_{\text{IN}} = 40\text{ V}$ | - | - | 400 600 | μA |
| MOSFET On-Resistance | $R_{\text{DS_ON}}$ | $V_{\text{DD}} = V_{\text{DDR}}, I_{\text{DRAIN}} = 120\text{ mA}$ | - | - | 40 60 | Ω |
| MOSFET Breakdown Voltage | V_{BR} | $V_{\text{DD}} = 8.5\text{ V}, I_{\text{DRAIN}} = 0.2\text{ mA}$ | 500 460 | - | - | V |
| Output Average Current | I_{AVG} | $V_{\text{DD}} = V_{\text{DDR}}$ | 114 112 | - | 126 128 | mA |
| Output Short Circuit Current | I_{SC} | $V_{\text{DD}} = V_{\text{DDR}}$ | 160 150 | - | 240 260 | mA |
| SW Minimum On-Time | $T_{\text{ON_MIN}}$ | $V_{\text{DD}} = V_{\text{DDR}}$ | - | - | 1000 | ns |
| SW Off-Time | T_{OFF} | $V_{\text{DD}} = V_{\text{DDR}}$ | 8 7 | - | 13 14 | μs |
| SW Blanking Time | T_{BLANK} | $V_{\text{DD}} = V_{\text{DDR}}$ | 200 | - | 400 | ns |
| Output Short Circuit Hiccup Time | T_{HICCUP} | $V_{\text{DD}} = V_{\text{DDR}}, I_{\text{DRAIN}} > 260\text{mA}$ | 350 280 | - | - | μs |

Note 1. Exceeding the absolute maximum ratings may damage the device.

Note 2. The device is not guaranteed to function outside its operating ratings.

Note 3. Stresses listed as the absolute maximum ratings may cause permanent damage to the device. These are for stress ratings. Functional operating of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may remain possibly to affect device reliability.

Note 4. Parameters are not 100% tested. Majority of all units meet this specification.

TYPICAL OPERATING CHARACTERISTICS

T.B.D.

REVISION NOTICE

The description in this datasheet can be revised without any notice to describe its electrical characteristics properly.